

EL - 23G

The EL - 23G, a high - power GaAs IRED mounted in a clear sidelooking package, is compact, low profile, and easy to mount.

FEATURES

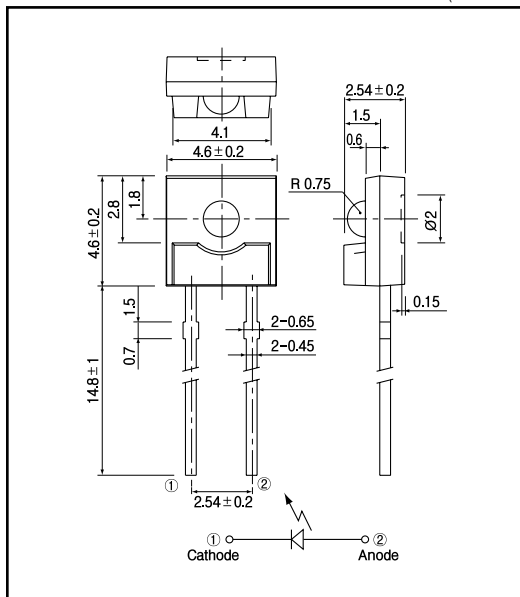
- Compact
- Low profile package
- Low - cost
- Sidelooking plastic package

APPLICATIONS

- Photointerrupters
- Optical switches
- Toys

DIMENSIONS

(Unit : mm)



MAXIMUM RATINGS

(Ta=25)

Item	Symbol	Rating	Unit
Reverse voltage	V _R	5	V
Forward current	I _F	60	mA
Pulse forward current ^{*1}	I _{FP}	1	A
Power dissipation	P _D	100	mW
Operating temp.	T _{opr.}	- 20 ~ + 100	
Storage temp.	T _{stg.}	- 30 ~ + 100	
Soldering temp. ^{*2}	T _{sol.}	240	

*1. pulse width : tw 100 ꝑec.period : T=10msec.

*2. For MAX.5 seconds at the position of 2 mm from the package

ELECTRO-OPTICAL CHARACTERISTICS

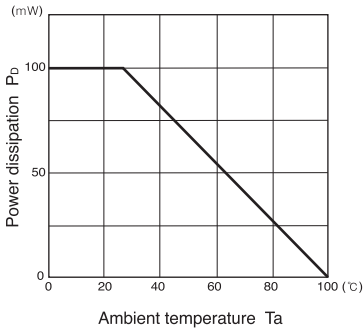
(Ta=25)

Item	Symbol	Conditions	Min.	Typ.	Max.	Unit.
Forward voltage	V _F	I _F =60mA		1.3	1.6	V
Reverse current	I _R	V _R =5V			10	µA
Capacitance	C _t	f=1MHz		25		pF
Radiant intensity	P ₀	I _F =60mA		2.0		mW/sr
Peak emission wavelength	ꝑ	I _F =60mA		940		nm
Spectral bandwidth 50%		I _F =60mA		50		nm
Half angle				± 30		deg.

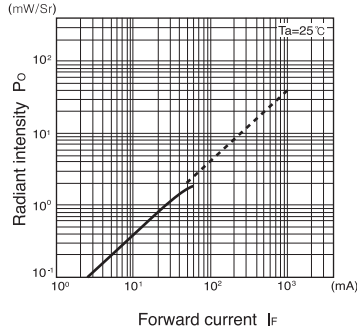
Infrared Emitting Diodes(GaAs)

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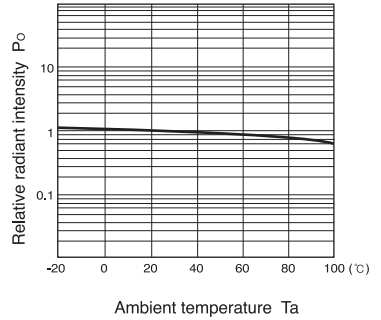
Power dissipation Vs. Ambient temperature



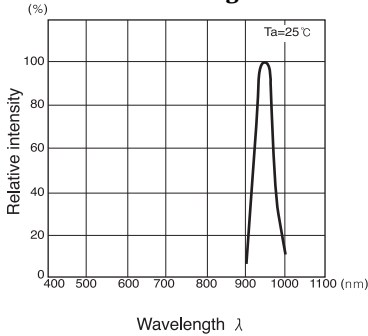
Radiant intensity Vs. Forward current



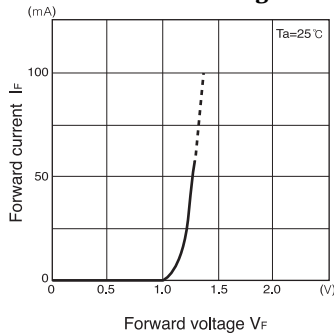
Relative radiant intensity Vs. Ambient temperature



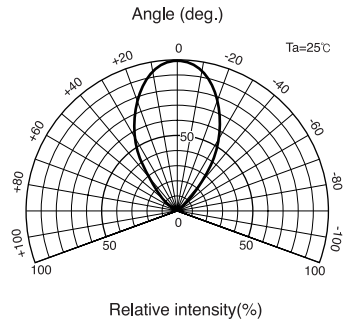
Relative intensity Vs. Wavelength



Forward current vs. Forward voltage



Radiant Pattern



Relative radiant intensity Vs. Distance

